

Electronic Supplementary Information (ESI)

Syntheses, Crystal Structures and Physical Properties of Three New Chalcogenides: $\text{NaGaGe}_3\text{Se}_8$, $\text{K}_3\text{Ga}_3\text{Ge}_7\text{S}_{20}$, and $\text{K}_3\text{Ga}_3\text{Ge}_7\text{Se}_{20}^\dagger$

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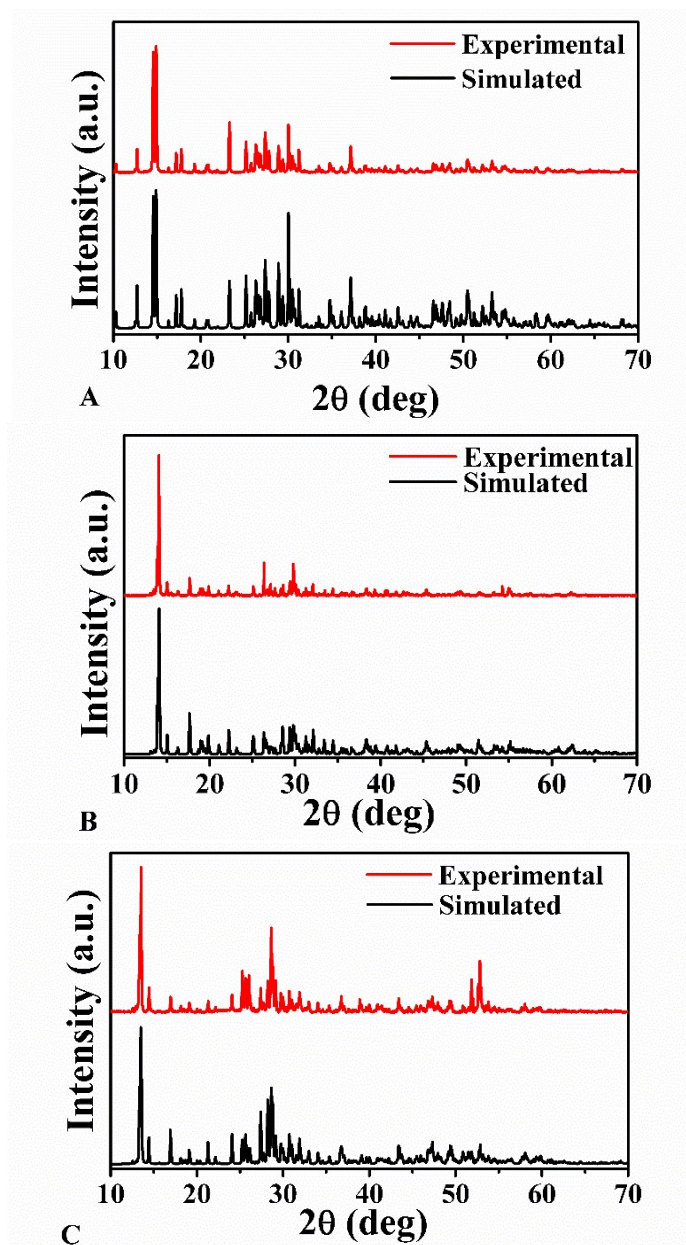


Fig. S1. Experimental (red) and simulated (black) X-ray powder diffraction data of NaGaGe₃Se₈, K₃Ga₃Ge₇S₂₀, and K₃Ga₃Ge₇Se₂₀. A: NaGaGe₃Se₈, B: K₃Ga₃Ge₇S₂₀, C: K₃Ga₃Ge₇Se₂₀.